

CURRENT MIRROR CIRCUIT

Background of the Invention

Field of the Invention

[0001]

5 The present invention relates to a current mirror circuit in an analog IC such as an LCD driver IC, which forms a large number of current sources placed in a wide area of an IC chip.

10 Description of the Related Art

[0002]

In an analog IC, when many constant current sources are required, a current mirror circuit which forms a large number of constant current sources with using one constant 15 current source as a reference is often used. Fig. 6A shows a conventional current mirror circuit which is usually used, and Fig. 6B is a characteristic diagram of the current mirror circuit of Fig. 6A.

[0003]

20 Referring to Fig. 6A, a constant reference potential V_{ref} is applied to the gate of a P-channel MOS field-effect transistor (hereinafter, "PMOS") Q0 to form a constant current source I_{61} . A constant current I_{ref} outputted from the constant current source I_{61} is supplied to an N-channel

MOS field-effect transistor (hereinafter, "NMOS") Qref6 in which the drain and the gate are connected to each other and the source is connected to the ground GND. The NMOS Qref6 is used as an input transistor (i.e., a mirror source 5 transistor) of the current mirror circuit, and NMOSs Q61 to Q6n are used as output transistors (i.e., mirror destination transistors). The sources of the output transistors Q61 to Q6n are connected to the source of the input transistor Qref6 through a feeder line Ws6. The 10 gates of the output transistors Q61 to Q6n are connected to the gate of the input transistor Qref6 through a potential line Wp6. According to the configuration, the gate potentials of the output transistors Q61 to Q6n are equal to the gate potential of the input transistor Qref6. The 15 figure "Vdd" denotes the power source potential.

[0004]

Even when a conductor wire such as an aluminum wire is used as the feeder line Ws6, the feeder line has wiring resistance R_w to some extent. In the case where a large 20 number of output transistors Q61 to Q6n are distributed in a wide range, the voltage drop due to the wiring resistance R_w and a current cannot be negligible. This state is shown in Fig. 6B.

[0005]

25 Referring to Fig. 6, no current flows through the

potential line W_{p6} , and hence the gate potentials of the output transistors Q_{61} to Q_{6n} are equal to the gate potential of the input transistor Q_{ref6} . On the other hand, because of the voltage drop in the feeder line W_{s6} ,

5 the source potentials of the output transistors Q_{61} to Q_{6n} are sequentially raised as moving along the placement positions of the output transistors Q_{61} to Q_{6n} . As compared with the gate-source voltage V_{gs} of the input transistor Q_{ref6} , therefore, the gate-source voltages V_{gs}

10 of the output transistors Q_{61} to Q_{6n} are sequentially smaller as moving along the placement positions. As a result, depending on the placement position, each of the output transistors Q_{61} to Q_{6n} is enabled to supply only a current of a level which is considerably different from a

15 desired current level.

[0006]

Fig. 7 shows a configuration in which feeder lines are arranged in a star-like shape in order to avoid the influence of the voltage drop caused by a feeder line. A

20 constant current I_{ref} output from a current source I_{71} is supplied to an NMOS Q_{ref7} in which the drain and the gate are connected to each other. The NMOS Q_{ref7} is used as an input transistor of a current mirror circuit, and NMOSs Q_{71} to Q_{7n} are used as output transistors. The sources of the

25 input transistor Q_{ref7} and the output transistors Q_{71} to

Q_{7n} are connected to a common point K through feeder lines W_{s7r} and W_{s71} to W_{s7n}, respectively, and then connected to the ground GND. According to the configuration, the gate-source voltages V_{gs} of the output transistors Q₇₁ to Q_{7n}
5 are equal to the gate-source voltage V_{gs} of the input transistor Q_{ref7}.

[0007]

Fig. 8 shows a configuration in which an interface based on a gate voltage is not produced and a current
10 interface is realized in order to avoid the influence of the voltage drop caused by a feeder line (see the following document "Design of Analog CMOS Integrated Circuits"). In a current mirror circuit having the current interface configuration of Fig. 8, a plurality "n" of or PMOSs Q₀₁ to Q_{0n} are disposed in a current source I₈₁, and a reference voltage V_{ref} is commonly applied to the gates so that a constant current I_{ref} is flown through each of the PMOSs Q₀₁ to Q_{0n}. The constant currents I_{ref} are supplied to NMOSs Q_{ref81} to Q_{ref8n} in each of which the drain and the
15 gate are connected to each other, and which are input transistors, through feeder lines W_{s81} to W_{s8n}, respectively. NMOSs Q₈₁ to Q_{8n} which are output transistors are connected to the input transistors Q_{ref81} to Q_{ref8n} so as to constitute respective current mirror
20 configurations. According to the configuration, regardless
25

of the difference among lengths of the feeder lines W_{S81} to W_{S8n} , i.e., different resistances, the same gate-source voltage V_{GS} is supplied to all the output transistors $Q81$ to $Q8n$. Therefore, a current of a desired level can be
5 supplied.

[0008]

Behzad Razavi, "Design of Analog CMOS Integrated Circuits" McGraw-Hill, 2001, Sec. 18.2 Analog Layout Techniques, p.p. 642-643 is known as a related document.

10 [0009]

In the conventional current mirror circuit of the star arrangement shown in Fig. 7, the feeder lines must be individually prepared and set so as to have the same length which is equal to the length of the longest feeder line, in
15 order to equalize the resistances of all the feeder lines W_{S7r} and W_{S71} to W_{S7n} . In the current mirror circuit of the current interface configuration shown in Fig. 8, the feeder lines W_{S81} to W_{S8n} whose number are equal to the number of the current mirror output transistors must be
20 individually disposed, and the current mirror configurations each of which is configured by input and output transistors must be produced. In the current mirror circuits of the conventional configurations of Figs. 7 and 8, when a large number of output transistors are disposed,
25 therefore, a large wiring area is required for forming the

feeder lines. In the case where hundreds of output transistors are used, such as in an LCD driver IC, a very large wiring area is required, and hence the chip size of the IC is increased.

5

Summary of the Invention

[0010]

An object of the invention is to provide a current mirror circuit which has a large number (such as hundreds) of output transistors, in which an influence due to the 10 wiring resistance of a feeder line can be remarkably reduced without increasing the wiring area for forming the feeder line.

[0011]

The invention provides a current mirror circuit, 15 which has a plurality of output transistors serving as current mirror outputs, including: a first input transistor whose one end is connected to a first constant current source and whose another end is connected to a first connecting position at a first potential, which is used as 20 an input side of a current mirror; a second input transistor whose one end is connected to a second constant current source, which is disposed with being separated from said first input transistor by a predetermined distance and is used as an input side of a current mirror; a first

feeder line which connects said other end of said first input transistor with another end of said second input transistor; a first potential line which connects said one end of said first input transistor with said one end of 5 said second input transistor with a resistance that is higher than a resistance of said first feeder line, to produce a potential gradient; and a plurality of output transistors distributed between said first input transistor and said second input transistor, which are coupled to said 10 first feeder line and said first potential line and are used as an output side of a current mirror.

[0012]

Moreover, the current mirror circuit further includes: a third input transistor whose one end is 15 connected to a third constant current source, which is disposed with being separated from said second input transistor by a predetermined distance in an opposite direction to said first input transistor and is used as an input of a current mirror; a second feeder line which 20 connects said other end of said second input transistor with another end of said third input transistor; a second potential line which connects said one end of said second input transistor with said one end of said third input transistor with a resistance that is higher than a 25 resistance of said second feeder line, to produce a

potential gradient; and a plurality of output transistors distributed between said second input transistor and said third input transistor, which are coupled to said second feeder line and said second potential line and is used as
5 an output side of a current mirror.

[0013]

Furthermore, said another end of said third input transistor is connected to a second connecting position at the first potential.

10 [0014]

Furthermore, said first potential line is polysilicon line and said second first potential line is polysilicon line.

[0015]

15 Furthermore, said first and second input transistors and said output transistors are P-channel MOS transistors and said third input transistor is also P-channel MOS transistor.

[0016]

20 Furthermore, said first and second input transistors and said output transistors are N-channel MOS transistors and said third input transistor is also N-channel MOS transistor.

Brief Description of the Drawings

Fig. 1A is a diagram showing the configuration of a current mirror circuit which is a first embodiment of the invention;

5 Fig. 1B is a view showing gate and source potentials in the current mirror circuit of Fig. 1A;

Fig. 2A is a diagram showing the configuration of a current mirror circuit which is a second embodiment of the invention;

10 Fig. 2B is a view showing gate and source potentials in the current mirror circuit of Fig. 2A;

Fig. 3A is a diagram showing the configuration of a current mirror circuit which is a third embodiment of the invention;

15 Fig. 3B is a view showing gate and source potentials in the current mirror circuit of Fig. 3A;

Fig. 4A is a diagram showing the configuration of a current mirror circuit which is a fourth embodiment of the invention;

20 Fig. 4B is a view showing gate and source potentials in the current mirror circuit of Fig. 4A;

Fig. 5 is a diagram showing another configuration example of the invention;

Fig. 6A is a diagram showing the configuration of a conventional current mirror circuit;

25 Fig. 6B is a characteristic diagram of the current

mirror circuit of Fig. 6A;

Fig. 7 is a diagram showing the configuration of another conventional current mirror circuit; and

5 Fig. 8 is a diagram showing the configuration of a further conventional current mirror circuit.

Detailed Description of the Preferred Embodiments

[0017]

Hereinafter, embodiments of the current mirror circuit according to the invention will be described with
10 reference to the drawings.

[0018]

(First Embodiment)

Fig. 1A shows the configuration of a current mirror circuit which is a first embodiment of the invention. The
15 current mirror circuit of shown in Fig. 1A is used for supplying a constant current to a large number or hundreds of buffers in an LCD driver IC or the like, and built in an IC chip. Fig. 1B is a view showing gate and source potentials in the current mirror circuit of Fig. 1A with
20 respect to the placement position.

[0019]

Referring to Fig. 1A, input transistors Qref1, Qref2, and Qref3 of the current mirror circuit, which are NMOS, are disposed in the left end, the center, and the right

end, respectively. In each of the input transistors Qref1, Qref2, and Qref3, the drain and the gate are connected to each other. The junctions between the drain and the gate of the input transistors Qref1, Qref2, and Qref3 are 5 connected one another through a high-resistance potential line Wp1. The sources of the input transistors Qref1, Qref2, and Qref3 are connected one another through a feeder line Ws1. The source of the input transistor Qref2 in the center is connected to a ground pin Pgnd to be connected to 10 the ground GND. The sources of the input transistors Qref1 and Qref3 in the left and right ends are not connected to the ground GND.

[0020]

Constant current sources I11 to I13, which 15 respectively have PMOSs Q01 to Q03, are connected to the drains of the input transistors Qref1, Qref2, and Qref3, respectively. A reference potential Vref generated in a reference voltage generating circuit 21 is applied to each gate of the PMOSs Q01 to Q03 through a gate signal line 22. 20 Therefore, constant currents Iref of the same level are supplied from the constant current sources I11 to I13 to the input transistors Qref1, Qref2, and Qref3, respectively. According to the configuration, the same gate-source voltage Vgs is generated between the gate and 25 the source of each of the input transistors Qref1, Qref2,

and Qref3.

[0021]

In the embodiment, the input transistors Qref1, Qref2, and Qref3 have the same size, and the constant currents Iref supplied to the transistors have the same level. However, the sizes of the transistors and the levels of the constant currents Iref are not particularly restricted as far as the gate-source voltages Vgs of the input transistors are equal in level to one another. This is applicable also to the other embodiments.

[0022]

In place of disposing the common reference voltage generating circuit 21 and the gate signal line 22, the constant current sources I11 to I13 themselves may include a voltage source. Alternatively, one of the current sources, and one of the input transistors (for example, the current source I11 and the transistor Qref1) may be configured as one current mirror source circuit so as to generate a predetermined gate-source voltage Vgs. These are also applicable to the other embodiments.

[0023]

Output transistors Q1 to Qj of the current mirror circuit, which are NMOS, are placed between the input transistor Qref1 in the left end and the input transistor Qref2 in the center. Similarly, output transistors Qj+1 to

Q_n of the current mirror circuit, which are NMOS, are placed between the input transistor Q_{ref2} in the center and the input transistor Q_{ref3} in the right end.

[0024]

5 The sources of the output transistors Q_1 to Q_n are connected to the feeder line W_{s1} and the gates of the same are connected to the potential line W_{p1} at the respective placement positions of the output transistors Q_1 to Q_n .
10 The drains of the output transistors Q_1 to Q_n are connected to respective load circuits, and the output transistors Q_1 to Q_n respectively operate so as to supply currents which are substantially proportional to the constant currents I_{ref} . When the output transistors Q_1 to Q_n are used in a driver IC for an LCD, they serve as constant current
15 sources for buffer circuits using a constant current.

[0025]

The sources of the input transistors Q_{ref1} to Q_{ref3} and the output transistors Q_1 to Q_n are sequentially connected one another through the feeder line W_{s1} having
20 low resistance such as an aluminum wire. There is a low wiring resistance R_w between the junctions.

[0026]

On the other hand, the gates of the input transistors Q_{ref1} to Q_{ref3} and the output transistors Q_1 to Q_n are
25 sequentially connected one another through the potential

line W_{p1} having a high resistance. Alternatively, the gates may be connected one another via resistors of high resistance R_g , or through a polysilicon line which itself has a high resistance. In any case, it is preferable that
5 the current flowing through the potential line W_{p1} is set to a level as low as possible, and further preferably to a level which is negligible as compared with the constant currents I_{ref} .

[0027]

10 In the current mirror circuit of Fig. 1A, when a current flows through each of the output transistors Q_1 to Q_n , as shown in Fig. 1B, the potentials of points of the feeder line W_{s1} are gradually raised in a curved manner in accordance with a product of the wiring resistance R_w and
15 the current, as further separated from the center grounding point.

[0028]

In the invention, the constant currents I_{ref} of the same level flow through the respective input transistors
20 Q_{ref1} to Q_{ref3} , and hence the gate-source voltages V_{gs} of the input transistors Q_{ref1} to Q_{ref3} are equal one another and have a predetermined value as shown in Fig. 1B.

[0029]

Therefore, the potentials of the potential line W_{p1} ,
25 i.e., the gate potentials of the output transistors Q_1 to

Q_n are potentials on the line connecting the potential of the center grounding point (i.e., the predetermined voltage V_{gs}), and the potential which is obtained by adding the predetermined gate-source voltage V_{gs} generated in the 5 input transistor Q_{ref1} or Q_{ref3} to the source potential in the left or right end. In other words, the potentials of the potential line W_{p1} have a constant potential gradient.

[0030]

As a result, as apparent from the comparison with the 10 conventional art of Fig. 6, the substantially predetermined voltage V_{gs} is applied between the gate and the source of each the output transistors Q_1 to Q_n although a small error may be produced because of the curved change. Therefore, the output transistors Q_1 to Q_n can supply a substantially 15 predetermined current to the respective loads. Further, unlike the prior art of Fig. 7 or 8, a influence due to the wiring resistance R_w of the feeder line W_{s1} can be remarkably reduced without increasing the wiring area for forming the feeder line W_{s1} .

20 [0031]

In the first embodiment of Fig. 1, also when the input transistor Q_{ref3} and the output transistors Q_{j+1} to Q_n on the side of the right end are omitted and only the configuration on the left side with respect to the center 25 is used, it is possible to attain the same effects as

described above.

[0032]

(Second Embodiment)

Fig. 2A shows the configuration of a current mirror circuit which is a second embodiment of the invention.

Fig. 2B is a view showing gate and source potentials in the current mirror circuit of Fig. 2A with respect to the placement position.

[0033]

In the second embodiment of Fig. 2, the sources of the input transistors Qref1 and Qref3 in the left and right ends are respectively connected to ground pins Pgnd1 and Pgnd2 to be connected to the ground GND. On the other hand, the source of the input transistor Qref2 in the center is not connected to the ground GND. In this way, the configuration of Fig. 2 is identical with that of Fig. 1 except the manner of connection (the place and the number of connections) to the ground GND.

[0034]

The second embodiment can attain the same effects as those of the embodiment of Fig. 1, and further attain the following effect. Even when one of the connections to the ground is broken for any reason, or when one of the ground pins cannot be used, the gate-source voltages Vgs of all the input transistors Qref1 to Qref3 can be maintained at

the predetermined value. Although the gate potential of the side where the connection to the ground is broken is raised, the whole current mirror circuit can operate without any trouble in the case where the raised gate
5 potential is within an allowable range.

[0035]

(Third Embodiment)

Fig. 3A shows the configuration of a current mirror circuit which is a third embodiment of the invention. Fig.
10 3B is a view showing gate and source potentials in the current mirror circuit of Fig. 3B with respect to the placement position.

[0036]

The third embodiment of Fig. 3 is different from the first embodiment of Fig. 1 in the following points. A fourth constant current source I14 is disposed between the first constant current source I11 and the second constant current source I12, and a fourth input transistor Qref4 is disposed between the first input transistor Qref1 and the second input transistor Qref2. A fifth constant current source I15 is disposed between the second constant current source I12 and the third constant current source I13, and a fifth input transistor Qref5 is disposed between the second input transistor Qref2 and the third input transistor
20 Qref3.
25

[0037]

In the third embodiment of Fig. 3, the gate-source voltages V_{GS} of the forth and fifth input transistors Q_{ref4} and Q_{ref5} also can be maintained to the predetermined value. As shown in Fig. 3B, potential gradient in the potential line W_{P1} are different between the input transistors Q_{ref1} to Q_{ref5} .

[0038]

Therefore, the third embodiment can attain the same effects as those of the first and second embodiments, and further attain the following effect. The gate-source voltages V_{GS} of the output transistors Q_1 to Q_n have a smaller error with respect to the predetermined voltage. Consequently, each current of the output transistors Q_1 to Q_n can be more correct level.

[0039]

(Fourth Embodiment)

Fig. 4A shows the configuration of a current mirror circuit which is a fourth embodiment of the invention. Fig. 4B is a view showing gate and source potentials in the current mirror circuit of Fig. 4B with respect to the placement position.

[0040]

The fourth embodiment of Fig. 4 is different from the third embodiment of Fig. 3 in the following points. The

sources of the input transistors Qref1 and Qref3 in the left and right ends are connected respectively to the ground pins Pgnd1 and Pgnd2 to be connected to the ground GND. In this way, the configuration of Fig. 4 is identical
5 with that of Fig. 3 except the manner of connection (the place and the number of connections) to the ground GND.

[0041]

The fourth embodiment of Fig. 4 can attain the same effects as those of the third embodiment of Fig. 3, and
10 further attain the following effect. As shown in Fig. 4B, the raised degrees of the gate potentials at all the placement positions can be suppressed to a small value, and hence the fourth embodiment can be effectively used even in the case where the power source voltage Vdd is low.

15 [0042]

In the embodiments described above, N-channel MOS transistors (NMOSS) are used in the current mirror circuit. Alternatively, a current mirror circuit in which P-channel MOS transistors (PMOSS) are used may be configured in the
20 same manner. Fig. 5 is a diagram showing an example of the configuration of a current mirror circuit which corresponds to the circuit of Fig. 1A, and in which PMOSSs are used. Fig. 5 is different from Fig. 1, only in that the NMOSSs are replaced with PMOSSs, and the voltage polarities and the
25 current directions are reversed. The corresponding

components are denoted by the identical reference numerals.

The circuit of Fig. 5 operates in the same manner as that of Fig. 1. The figure "Pvdd" denotes a power source pin.

[0043]

5 As explained above, in the current mirror circuit of the invention, a first input transistor (Qref1) whose one end is connected to a first constant current source (I11) and whose another end is connected to a reference potential (for example, the ground) is used as an input side of a
10 current mirror. A second input transistor (Qref2) whose one end is connected to a second constant current source (I12) is disposed with being separated from the first input transistor (Qref1) by a predetermined distance and is also used as an input side of a current mirror. A plurality of
15 output transistors (Q1 to Qj) are used as an output side of a current mirror and are distributed between the first and second input transistors (Qref1 and Qref2). According to the configuration, the gate-source voltages Vgs of the plural output transistors (Q1 to Qj) are substantially
20 equal to those of the first and second input transistors (Qref1 and Qref2), and an influence due to the wiring resistance (Rw) of a feeder line (Ws) can be remarkably reduced without increasing the wiring area for forming the feeder line (Ws).